

NTTFS4C02N

MOSFET – Power, Single, N-Channel, μ 8FL 30 V, 170 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- Power Load Switch
- Notebook Battery Management

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Symbol | Value | Unit | |
|--|--|--------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DSS} | 30 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\theta JA}$ (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 29 | A |
| | | $T_A = 85^\circ\text{C}$ | 21 | |
| Power Dissipation $R_{\theta JA}$ (Note 1) | P_D | 2.7 | W | |
| Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 36 | A |
| | | $T_A = 85^\circ\text{C}$ | 26 | |
| Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1) | P_D | 4.2 | W | |
| Continuous Drain Current $R_{\theta JA}$ (Note 2) | I_D | $T_A = 25^\circ\text{C}$ | 16 | A |
| | | $T_A = 85^\circ\text{C}$ | 12 | |
| Power Dissipation $R_{\theta JA}$ (Note 2) | P_D | 0.83 | W | |
| Continuous Drain Current $R_{\theta JC}$ (Note 1) | I_D | $T_C = 25^\circ\text{C}$ | 170 | A |
| | | $T_C = 85^\circ\text{C}$ | 120 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | P_D | 91 | W | |
| Pulsed Drain Current | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | I_{DM} | 500 | A |
| Operating Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 100 | A | |
| Drain to Source dV/dt | dV/dt | 6.0 | V/ns | |
| Single Pulse Drain-to-Source Avalanche Energy ($I_L = 37 A_{pk}$) (Note 3) | E_{AS} | 162 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

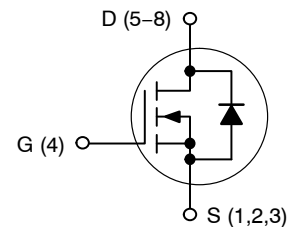


ON Semiconductor®

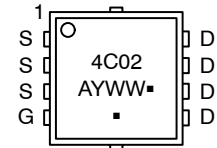
www.onsemi.com

| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | I_D MAX |
|---------------|------------------------|-----------|
| 30 V | 2.25 m Ω @ 10 V | 170 A |
| | 3.1 m Ω @ 4.5 V | |

N-Channel MOSFET



MARKING DIAGRAM



4C02 = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|---------------|-----------------|--------------------|
| NTTFS4C02NTAG | WDFN8 (Pb-Free) | 1500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTTFS4C02N

- Surface-mounted on FR4 board using the minimum recommended pad size.
- This is the absolute maximum ratings. Parts are 100% tested at $T_J = 25^\circ\text{C}$, $V_{GS} = 10\text{ V}$, $I_L = 36\text{ A}$, $E_{AS} = 65\text{ mJ}$.

THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|--------------------|
| Junction-to-Case (Drain) | $R_{\theta JC}$ | 1.4 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – Steady State (Note 4) | $R_{\theta JA}$ | 46 | |
| Junction-to-Ambient – Steady State (Note 5) | $R_{\theta JA}$ | 150 | |
| Junction-to-Ambient – ($t \leq 10\text{ s}$) (Note 4) | $R_{\theta JA}$ | 30 | |

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|---|-------------------|---|---------------------------|------|-----|----------------------------|
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$ | 30 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | 13.8 | | $\text{mV}/^\circ\text{C}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}$, $V_{DS} = 24\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 1.0 | μA |
| | | | $T_J = 125^\circ\text{C}$ | | 10 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}$, $V_{DS} = 30\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 10 | μA |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}$, $V_{GS} = 20\text{ V}$ | | | 100 | nA |

ON CHARACTERISTICS (Note 6)

| | | | | | | |
|--|------------------|---|---------------------|-----|------|----------------------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$ | 1.3 | 1.6 | 2.2 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 5.0 | | $\text{mV}/^\circ\text{C}$ |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 20\text{ A}$ | 1.9 | 2.25 | $\text{m}\Omega$ |
| | | $V_{GS} = 4.5\text{ V}$ | $I_D = 20\text{ A}$ | 2.7 | 3.1 | |
| Forward Transconductance | g_{FS} | $V_{DS} = 1.5\text{ V}$, $I_D = 50\text{ A}$ | | 140 | | S |
| Gate Resistance | R_G | | | 0.9 | | Ω |

CHARGES AND CAPACITANCES

| | | | | | | |
|------------------------------|-------------------|--|--|-------|--|-------------|
| Input Capacitance | C_{ISS} | $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$, $V_{DS} = 15\text{ V}$ | | 2980 | | pF |
| Output Capacitance | C_{OSS} | | | 1200 | | |
| Reverse Transfer Capacitance | C_{RSS} | | | 55 | | |
| Output Charge | Q_{OSS} | $V_{GS} = 0\text{ V}$, $V_{DD} = 15\text{ V}$ | | 25 | | nC |
| Capacitance Ratio | C_{RSS}/C_{ISS} | $V_{GS} = 0\text{ V}$, $V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$ | | 0.018 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 50\text{ A}$ | | 20 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 4.7 | | |
| Gate-to-Source Charge | Q_{GS} | | | 8.5 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 4 | | |
| Gate Plateau Voltage | V_{GP} | | | 2.8 | | V |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 50\text{ A}$ | | 45 | | nC |

SWITCHING CHARACTERISTICS (Note 7)

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

NTTFS4C02N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|--------------|--|-----|-----|-----|------|
| SWITCHING CHARACTERISTICS (Note 7) | | | | | | |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 50\text{ A}, R_G = 3.0\ \Omega$ | | 12 | | ns |
| Rise Time | t_r | | | 116 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 25 | | |
| Fall Time | t_f | | | 10 | | |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 50\text{ A}, R_G = 3.0\ \Omega$ | | 9 | | ns |
| Rise Time | t_r | | | 102 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 33 | | |
| Fall Time | t_f | | | 6 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|----------|---|---------------------------|----|-----|-----|---|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V},$ $I_S = 20\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.8 | 1.1 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.6 | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 50\text{ A}$ | | 42 | | ns | |
| Charge Time | t_a | | | 21 | | | |
| Discharge Time | t_b | | | 21 | | | |
| Reverse Recovery Charge | Q_{RR} | | | 28 | | nC | |

6. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

7. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NTTFS4C02N

TYPICAL CHARACTERISTICS

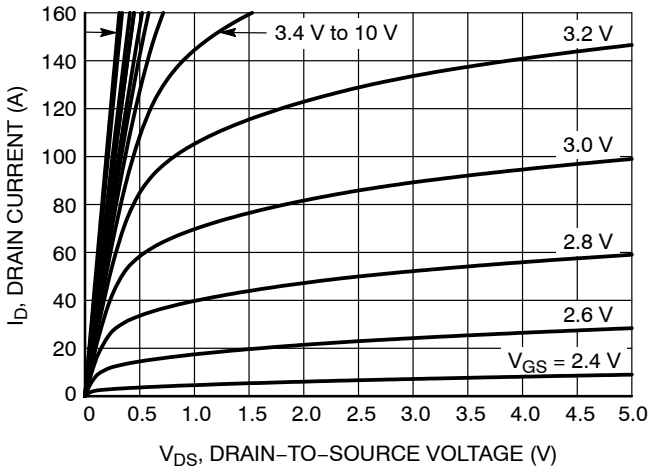


Figure 1. On-Region Characteristics

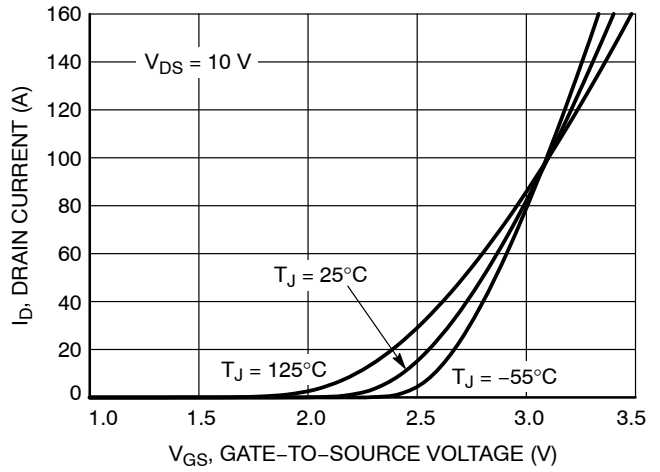


Figure 2. Transfer Characteristics

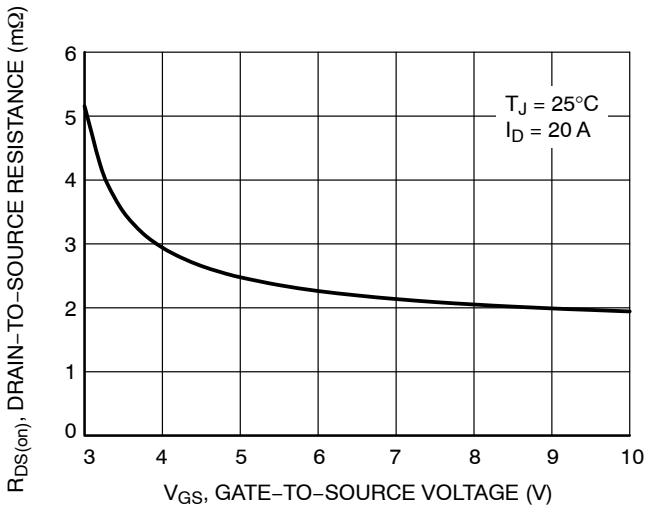


Figure 3. On-Resistance vs. Gate-to-Source Voltage

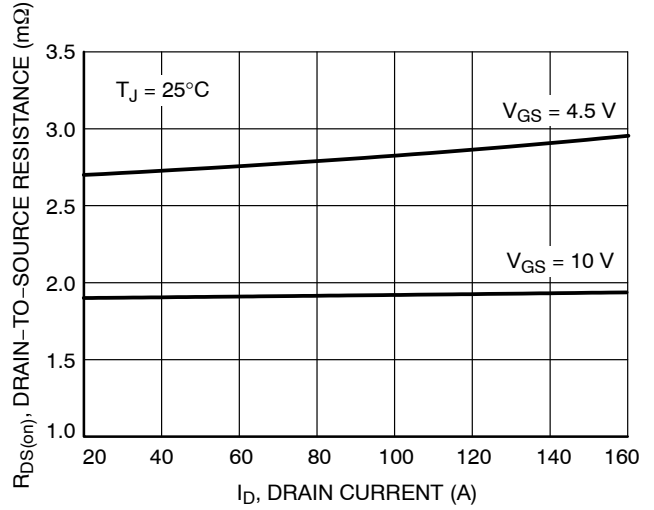


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

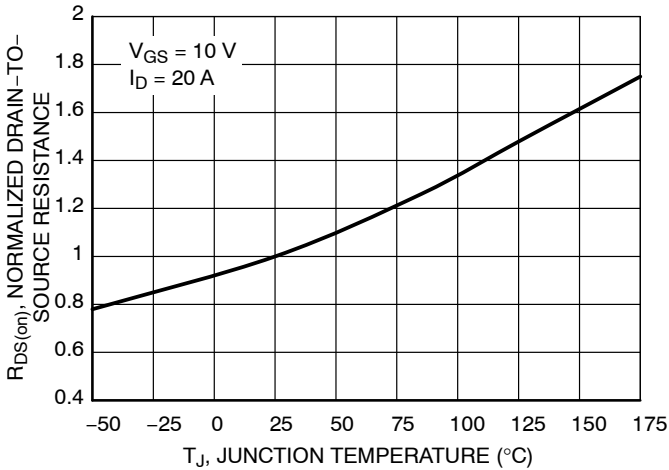


Figure 5. On-Resistance Variation with Temperature

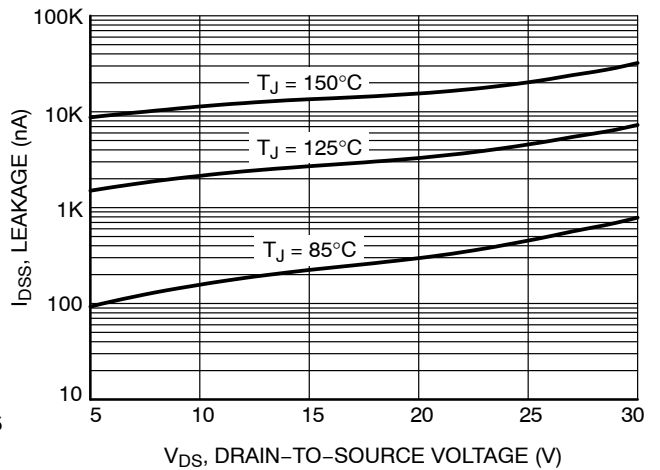


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTTFS4C02N

TYPICAL CHARACTERISTICS

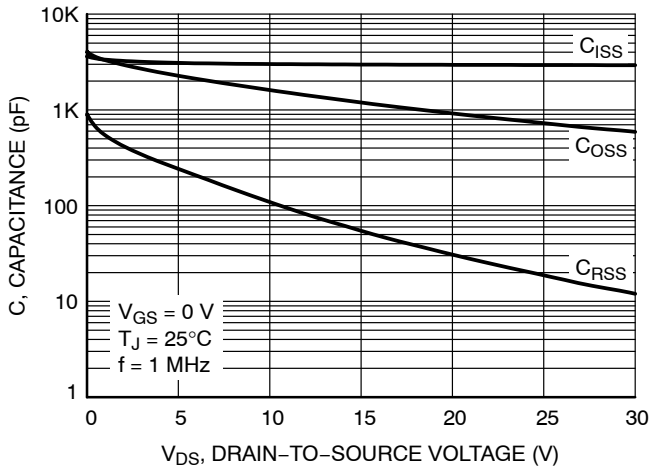


Figure 7. Capacitance Variation

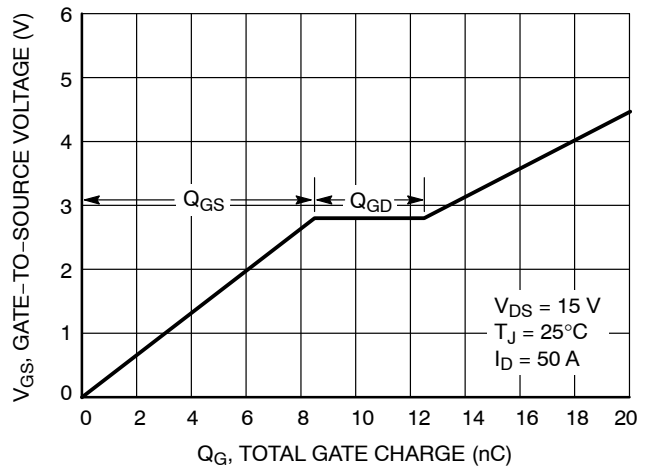


Figure 8. Gate-to-Source vs. Total Charge

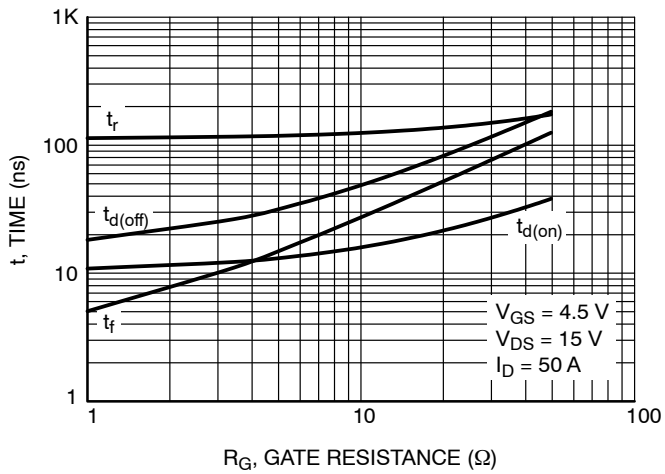


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

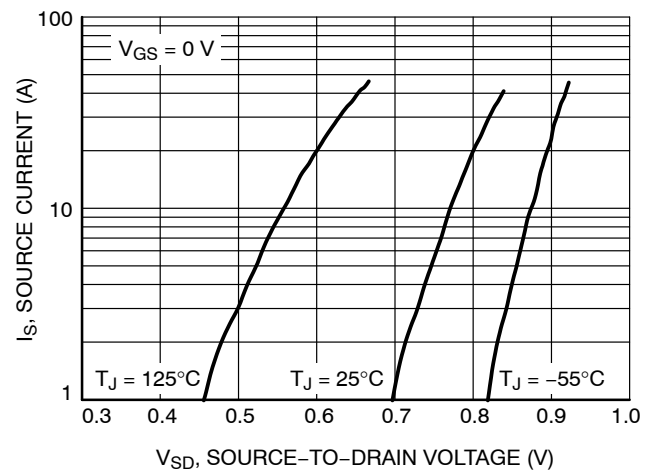


Figure 10. Diode Forward Voltage vs. Current

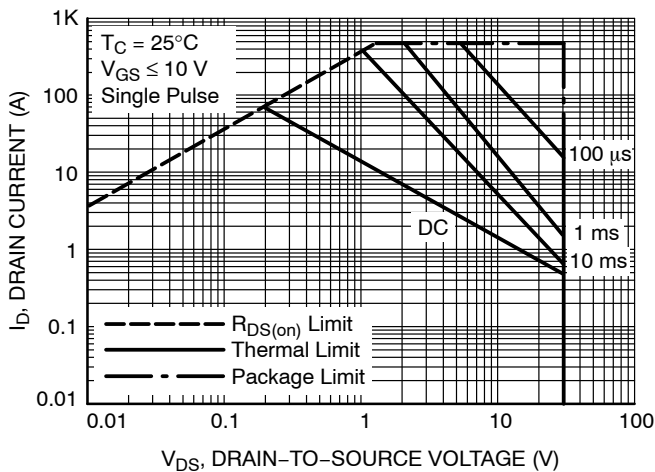


Figure 11. Maximum Rated Forward Biased Safe Operating Area

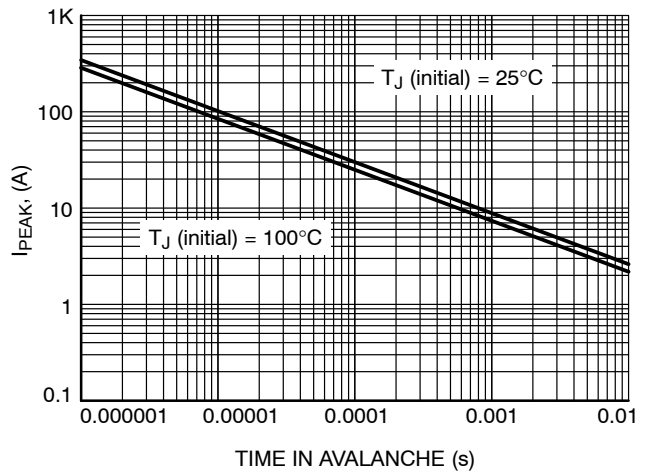


Figure 12. I_{PEAK} vs. Time in Avalanche

NTTFS4C02N

TYPICAL CHARACTERISTICS

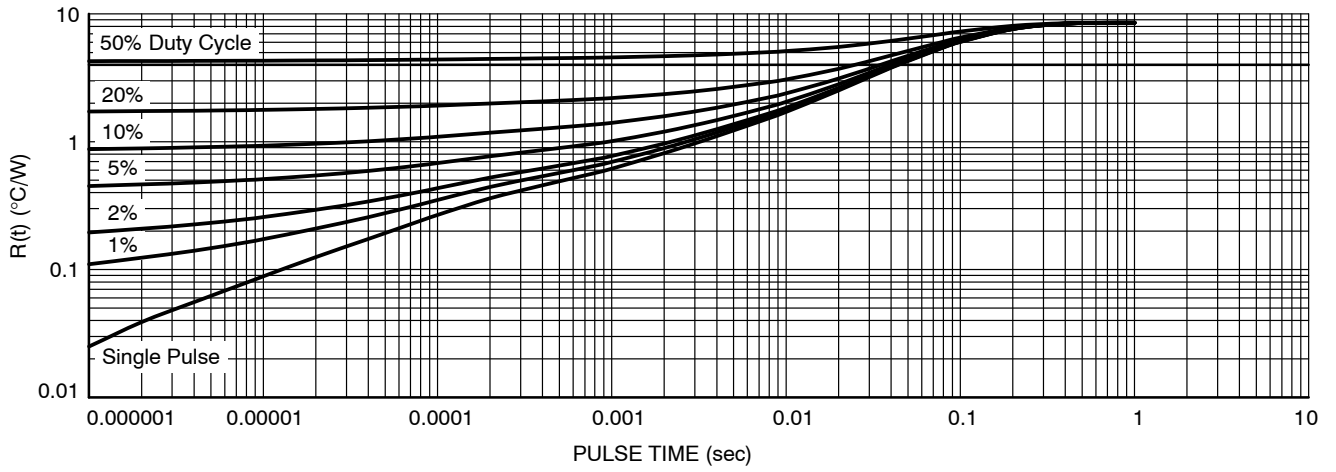
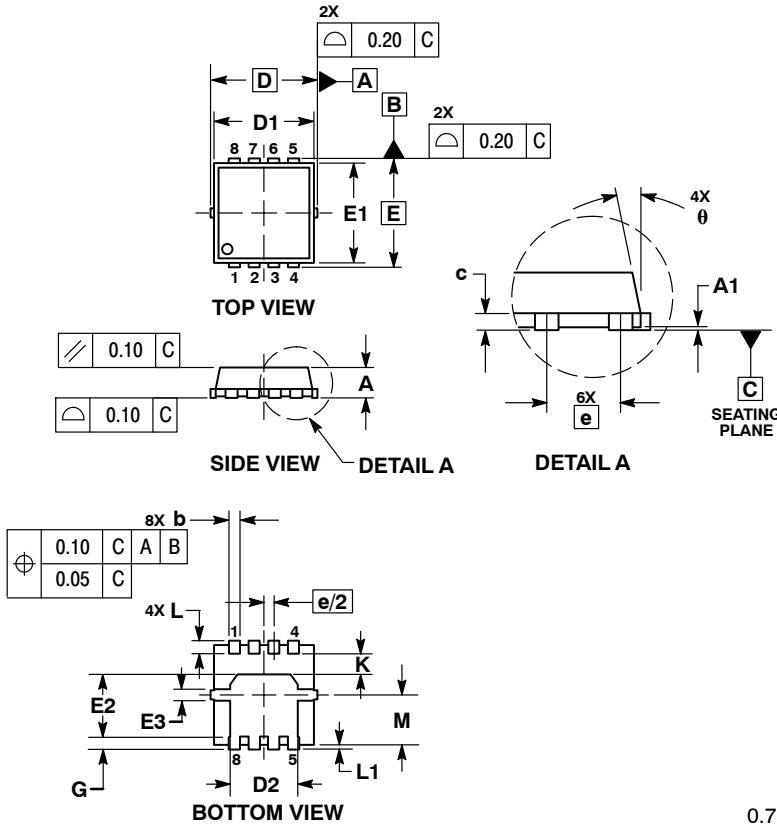


Figure 13. Thermal Characteristics

NTTFS4C02N

PACKAGE DIMENSIONS

WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

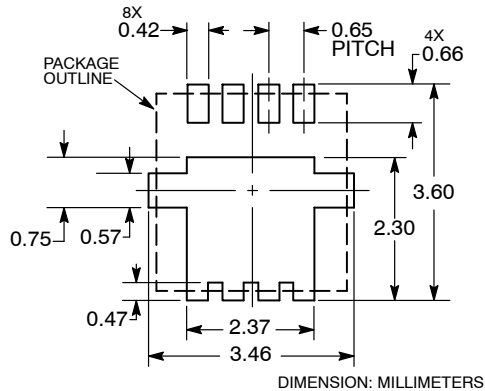


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|----------|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.031 |
| A1 | 0.00 | --- | 0.05 | 0.000 | --- | 0.002 |
| b | 0.23 | 0.30 | 0.40 | 0.009 | 0.012 | 0.016 |
| c | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| D | 3.30 BSC | | | 0.130 BSC | | |
| D1 | 2.95 | 3.05 | 3.15 | 0.116 | 0.120 | 0.124 |
| D2 | 1.98 | 2.11 | 2.24 | 0.078 | 0.083 | 0.088 |
| E | 3.30 BSC | | | 0.130 BSC | | |
| E1 | 2.95 | 3.05 | 3.15 | 0.116 | 0.120 | 0.124 |
| E2 | 1.47 | 1.60 | 1.73 | 0.058 | 0.063 | 0.068 |
| E3 | 0.23 | 0.30 | 0.40 | 0.009 | 0.012 | 0.016 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| G | 0.30 | 0.41 | 0.51 | 0.012 | 0.016 | 0.020 |
| K | 0.65 | 0.80 | 0.95 | 0.026 | 0.032 | 0.037 |
| L | 0.30 | 0.43 | 0.56 | 0.012 | 0.017 | 0.022 |
| L1 | 0.06 | 0.13 | 0.20 | 0.002 | 0.005 | 0.008 |
| M | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| θ | 0° | --- | 12° | 0° | --- | 12° |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to its products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative